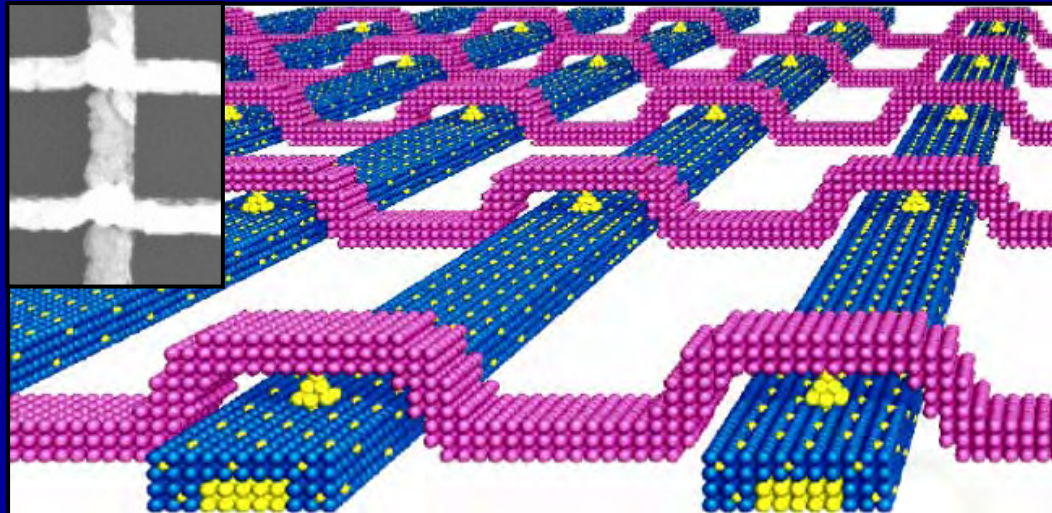




2008.3.6

Atomic Switch for making new type of electronic devices and systems

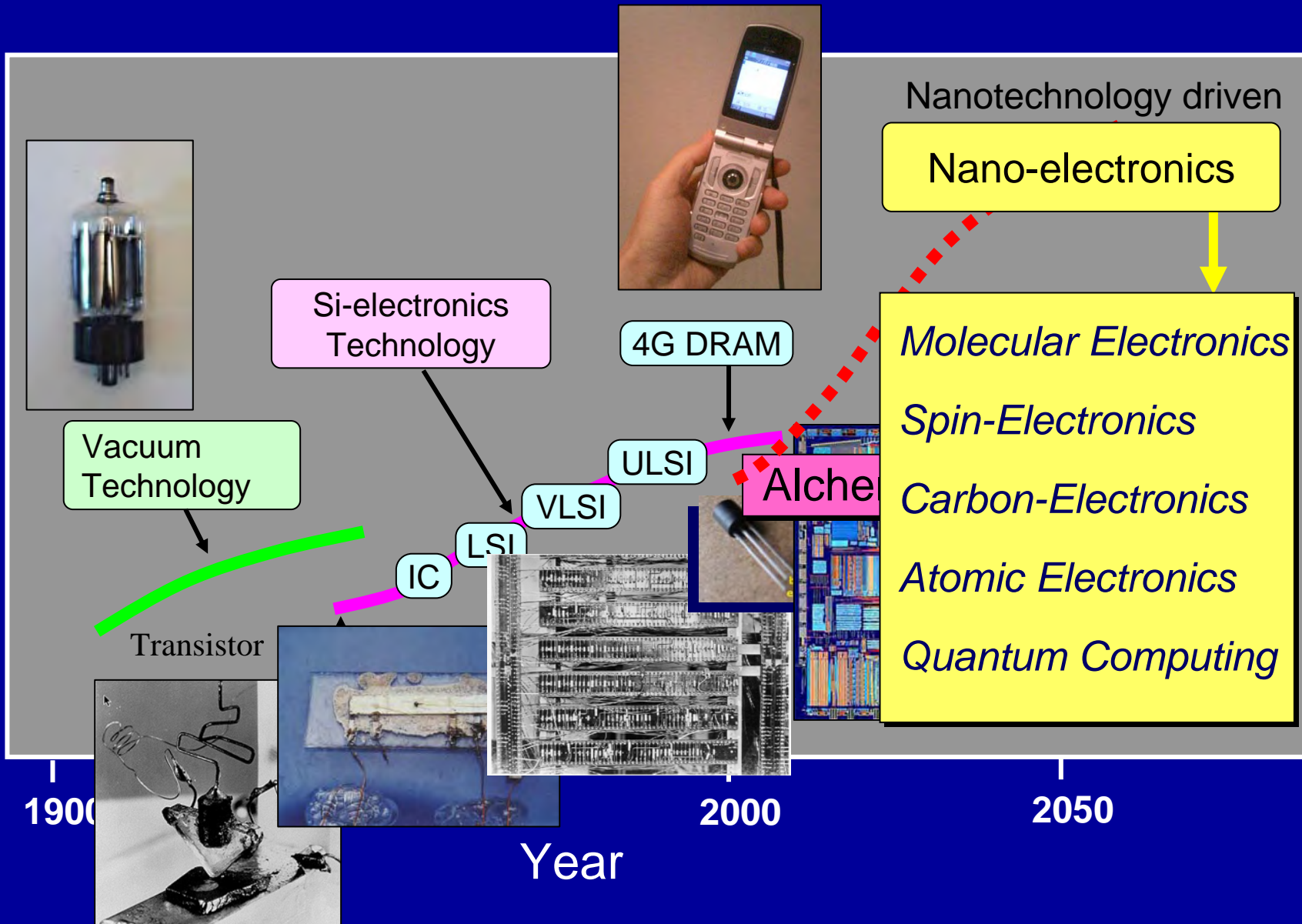


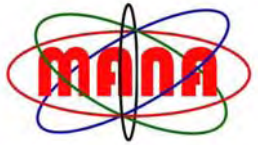
Tsuyoshi Hasegawa
WPI Center for Materials Nanoarchitectonics
National Institute for Materials Science, Japan



Further Progress by Nanotechnology

Performance



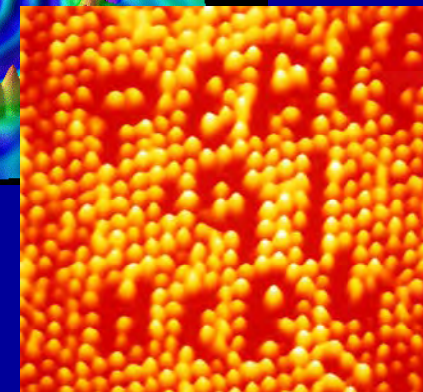
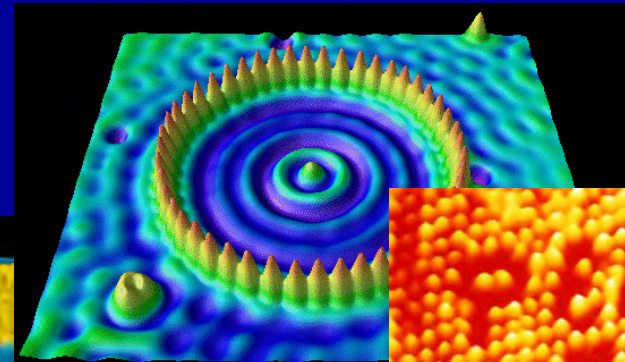
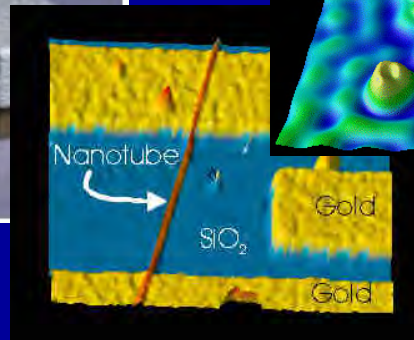
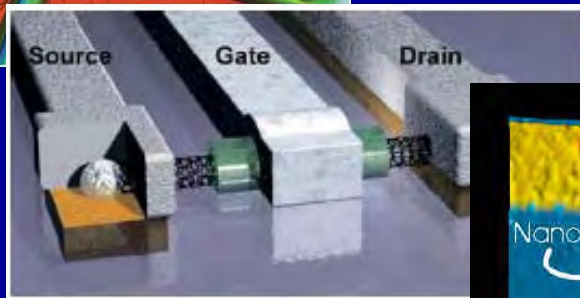
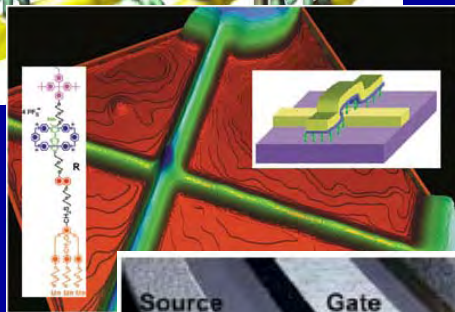
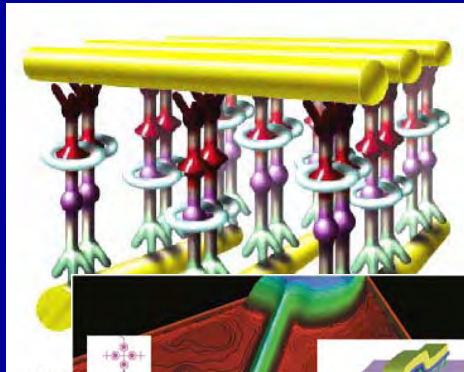


Key point for the further progress

Miniaturization

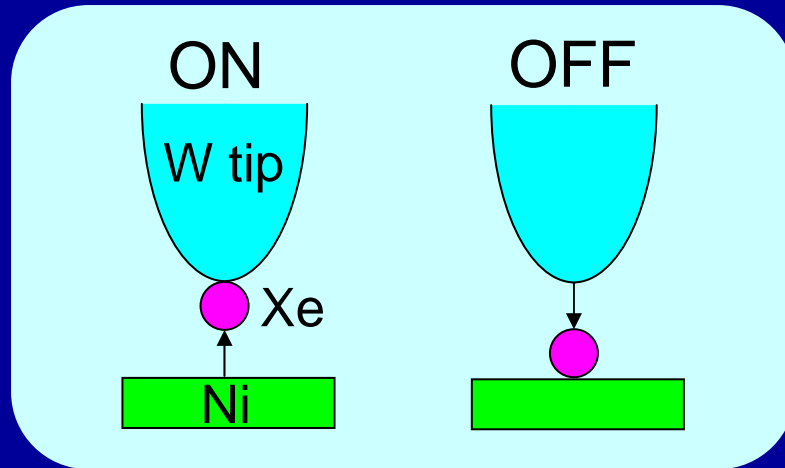


Using new functions
by new materials &
new structures





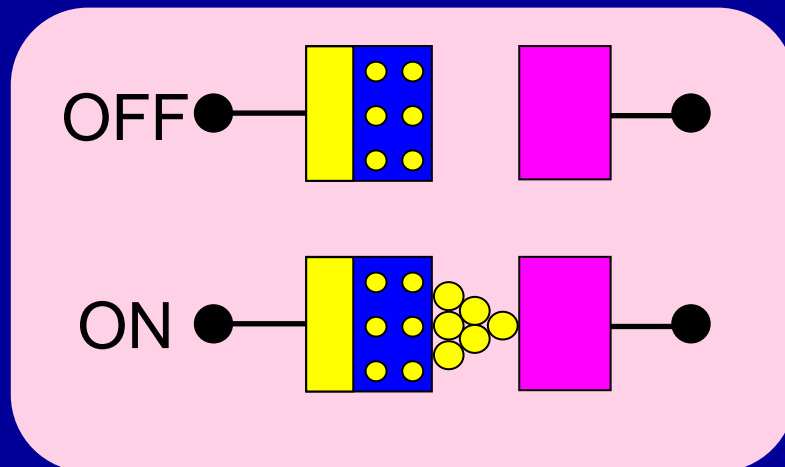
Atomic Switch



D. M. Eigler *et al.*, Nature **352** (1991) 600.

Atomic movement was achieved by electrical field.

ON/OFF : 10



K. Terabe *et al.*, Nature **433** (2005) 47.

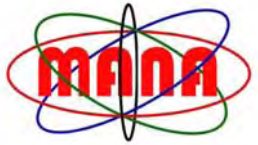
Atomic movement was achieved by solid electrochemical reaction.

ON/OFF : $>10^3$



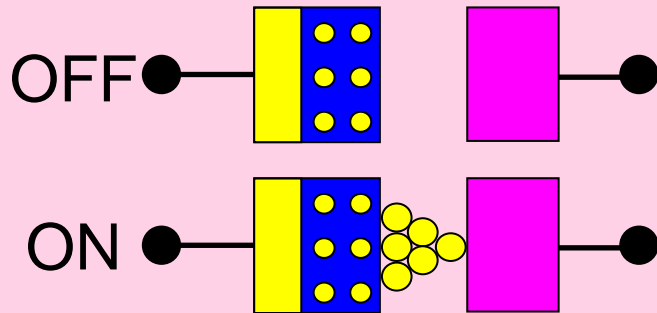
OUTLINE

- 1. Mechanism and Characteristics**
- 2. Application for Commercial Devices**
- 3. New Type of Atomic Switch**



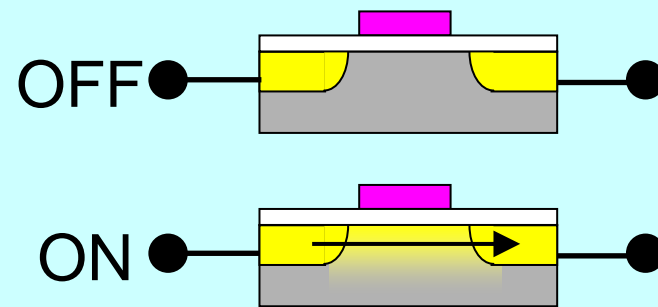
Small Size and Low On-resistance

Atomic switch

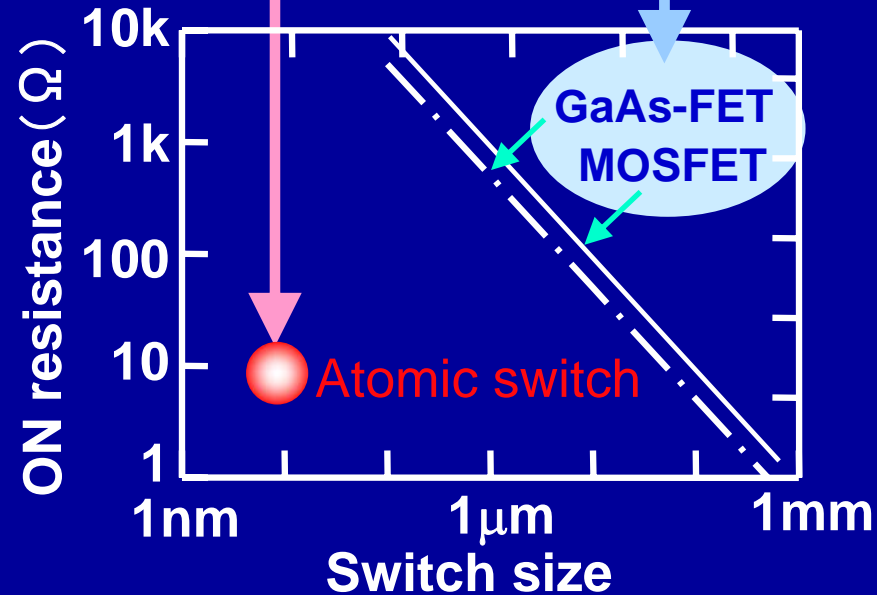


Atomic movement is controlled.

Semiconductor Switch

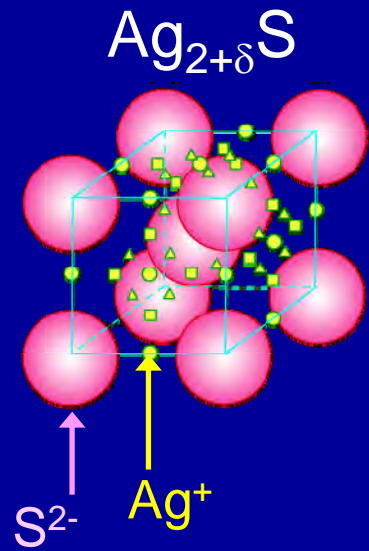


Electronic distribution is controlled

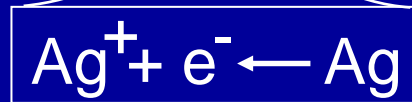
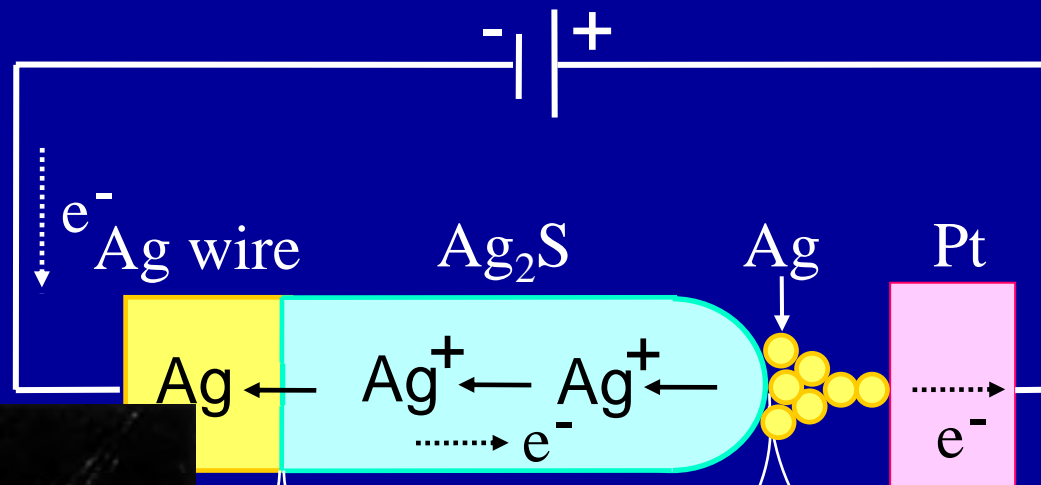


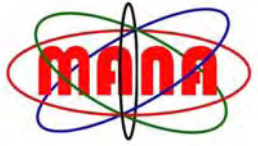


Operating Mechanism

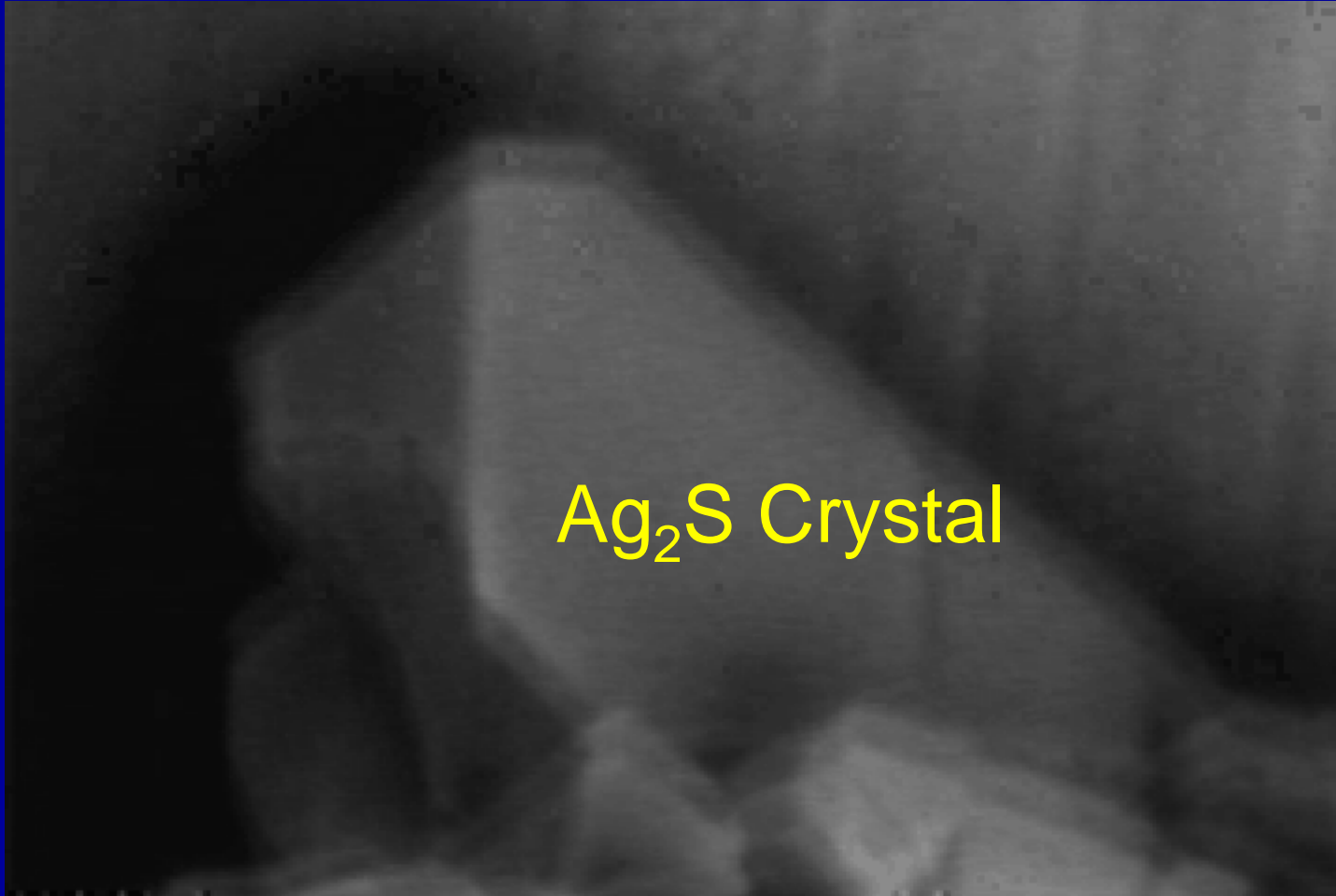


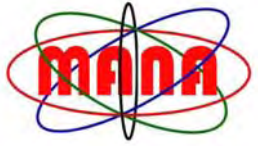
switched off



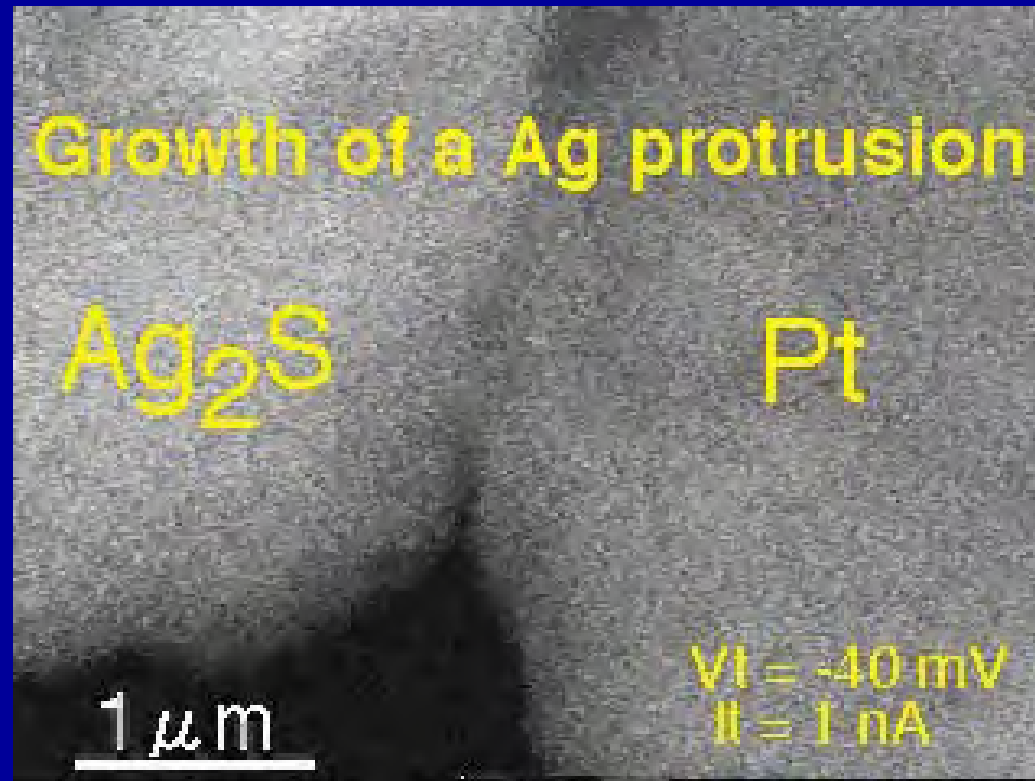


Ag nanowire growth by e-beam

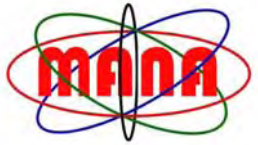




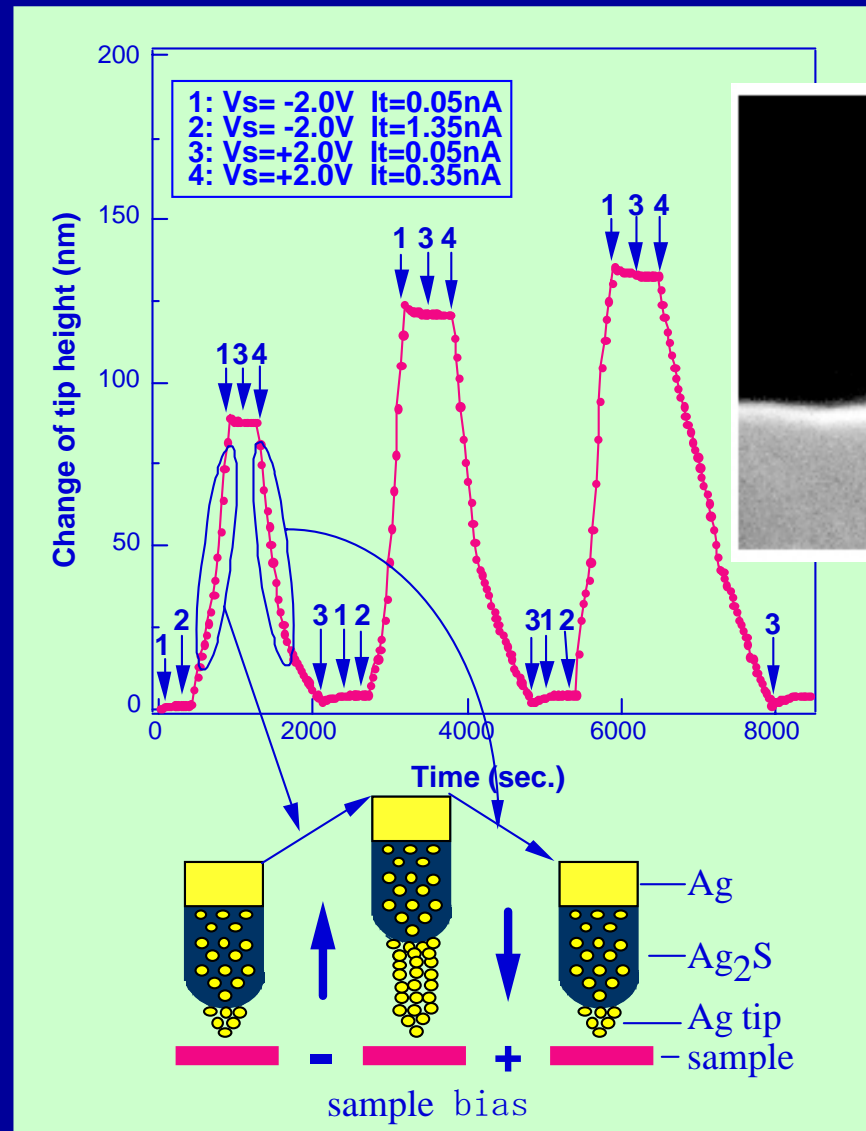
Single Ag protrusion growth by STM



The two electrodes are fixed in the case of atomic switch operation.



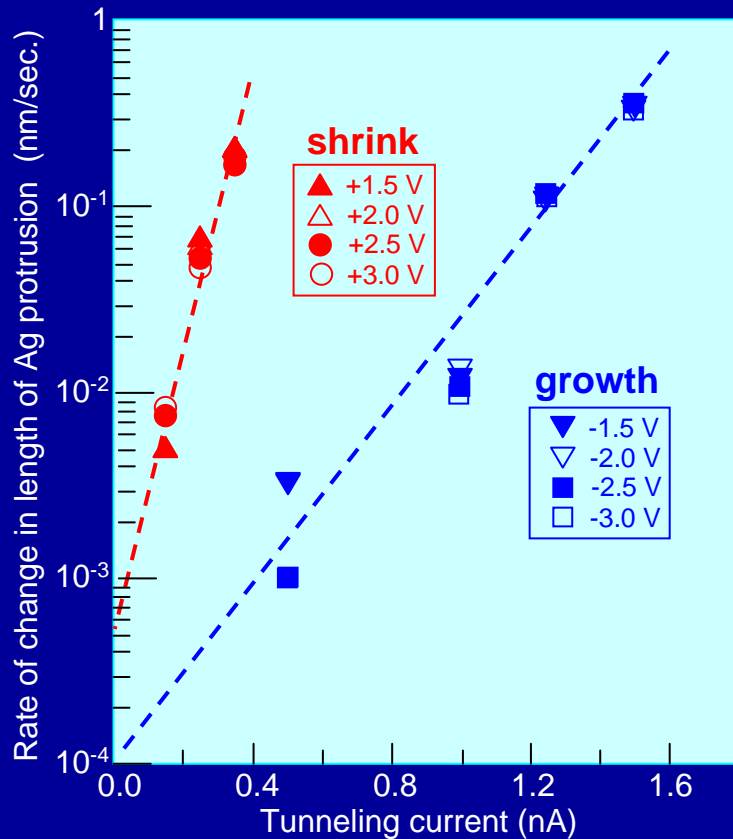
Controlled growth and shrinkage



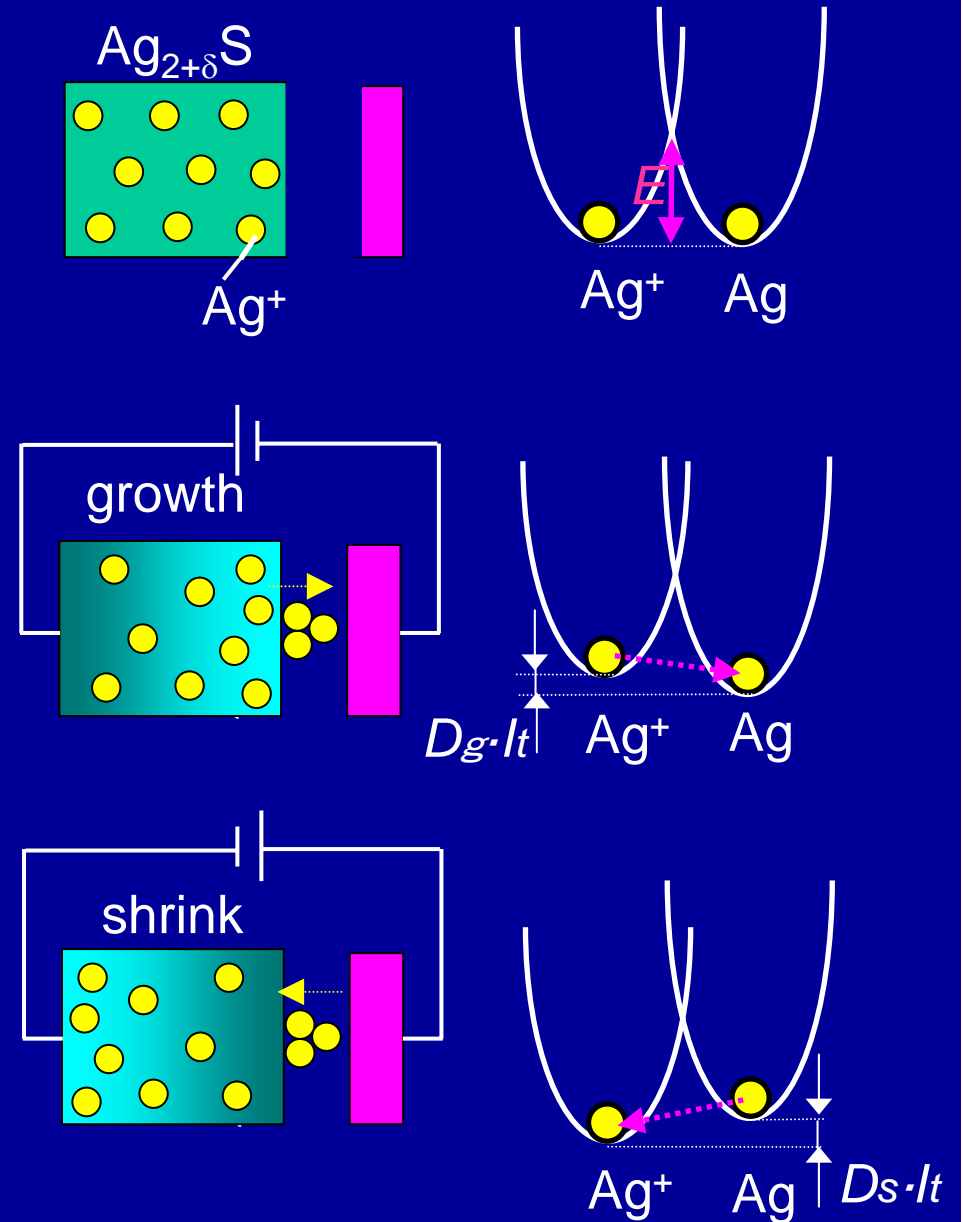
K. Terabe, T. Nakayama, T. Hasegawa and M. Aono, J. Appl. Phys., 91 (2002) 10110.

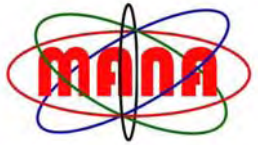


Growth and Shrinkage speed of Ag



$$\frac{dN}{dt} = A \cdot \exp\left(\frac{E - D \cdot It}{kT}\right)$$

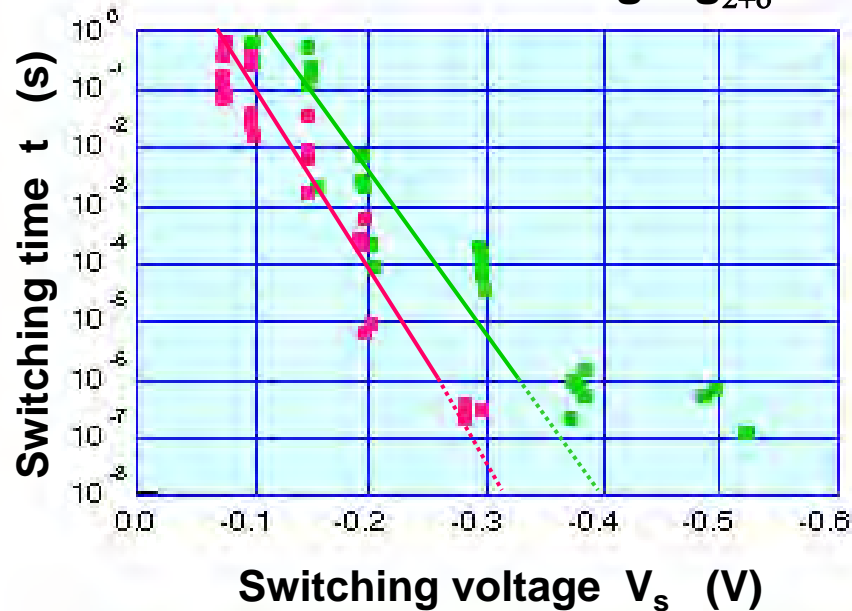




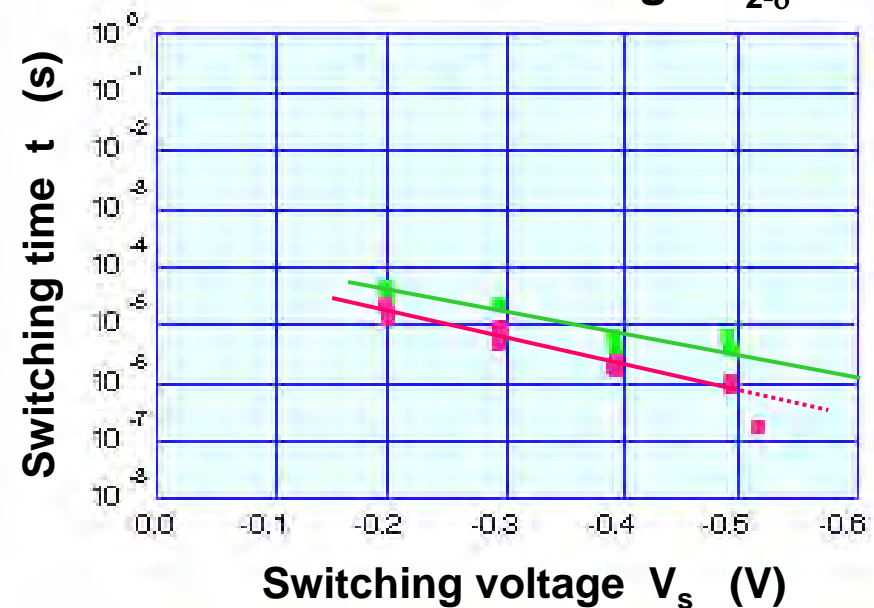
Switching time vs. switching voltage

Switching characteristics depend on the materials.

Atomic switch using $\text{Ag}_{2+\delta}\text{S}$



Atomic switch using $\text{Cu}_{2-\delta}\text{S}$



■ : 1MΩ to 12.9 kΩ

■ : 100 kΩ to 12.9 kΩ

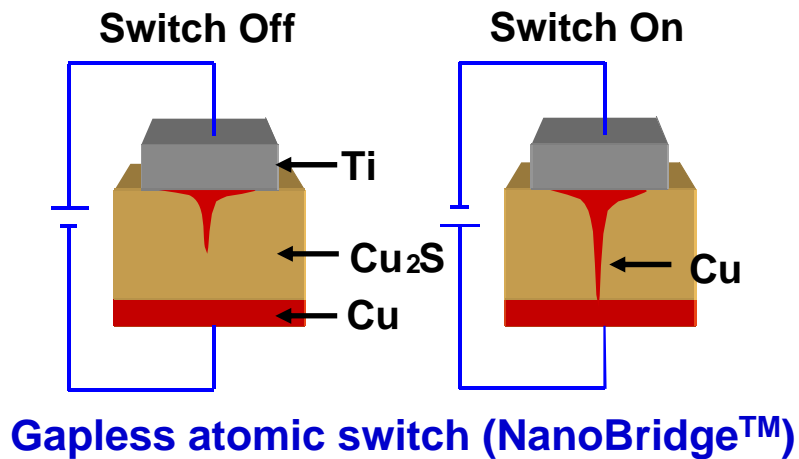
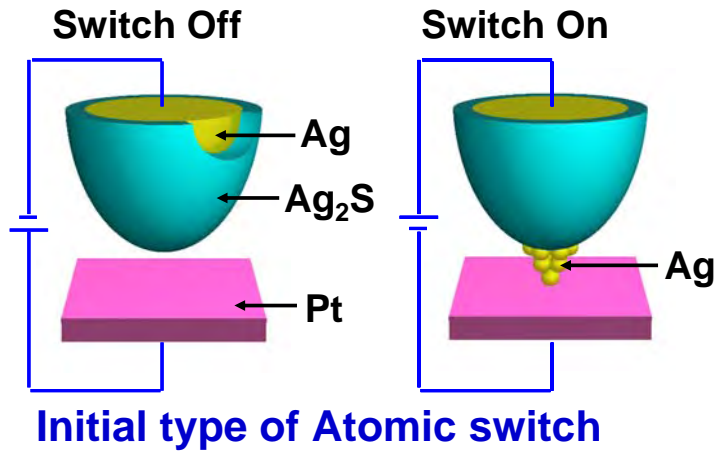
T. Tamura, T. Hasegawa, K. Terabe, T. Nakayama, T. Sakamoto, H. Sunamura, H. Kawaura, S. Hosaka and M. Aono, Jpn. J. Appl. Phys. 45 (2006) L364.



Two types of atomic switch

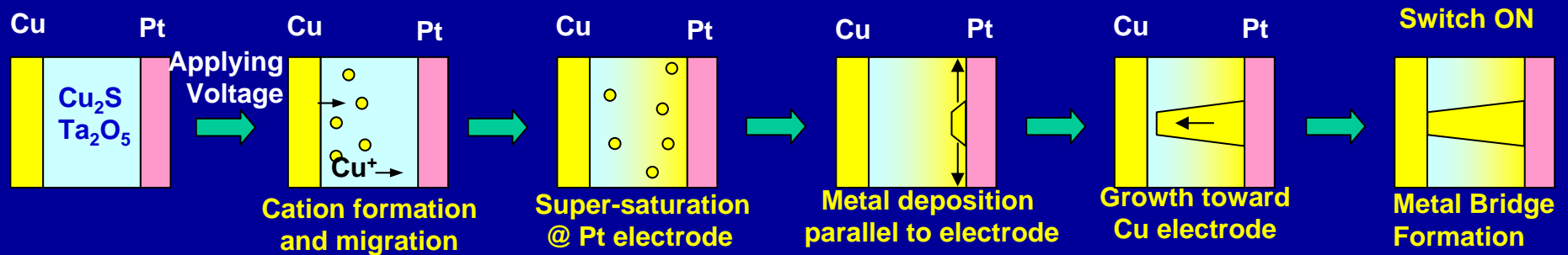
NEC

‘with gap’ and ‘without gap’



Switching Mechanism of gapless atomic switch

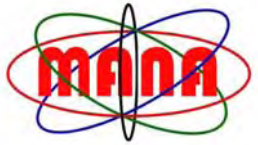
Operating Model





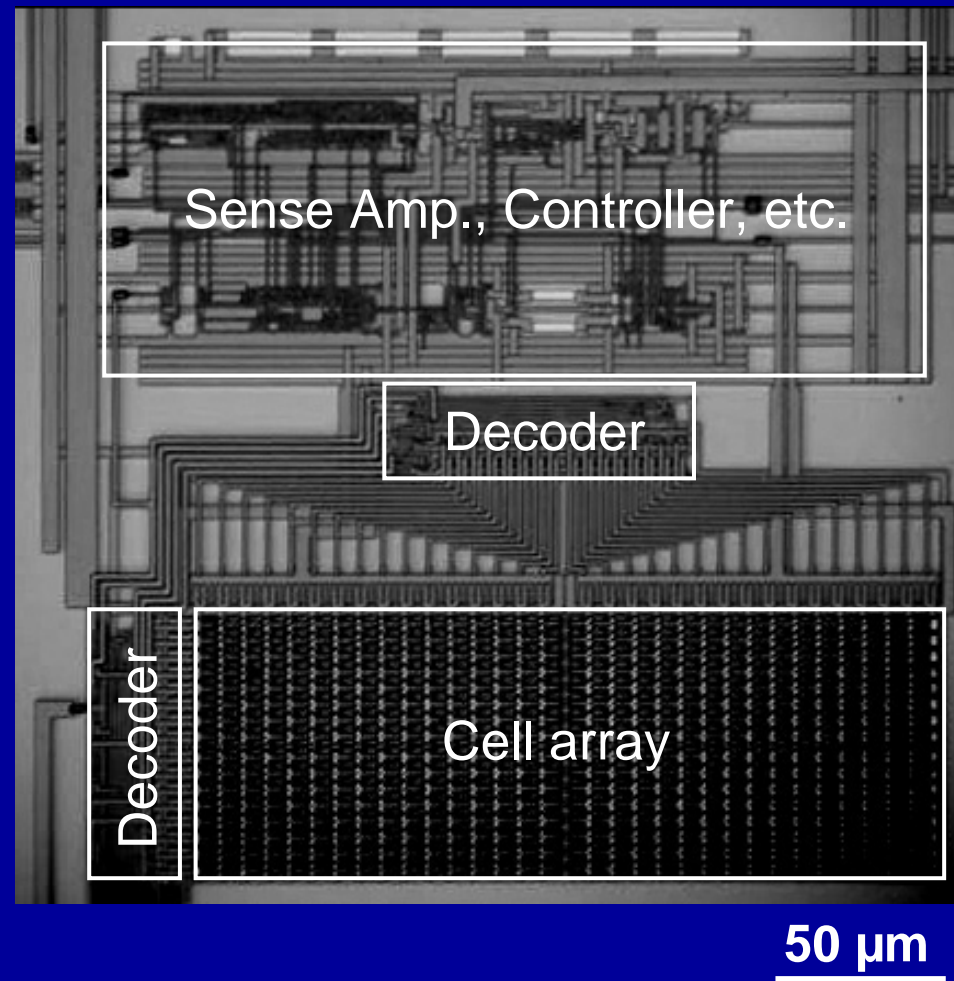
OUTLINE

1. Mechanism and Characteristics
- 2. Application for Commercial Devices**
3. New Type of Atomic Switch



1 k-bit nonvolatile memory

NEC



T. Sakamoto, H. Sunamura, M. Mizuno, H. Kawaura, T. Hasegawa, K. Terabe, T. Nakayama and M. Aono, IEEE J. Solid-State Circuits 40 (2005) 168.

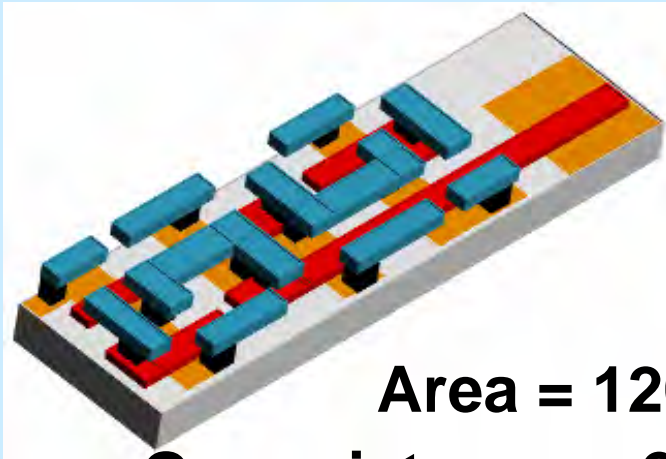


Apply to Programmable Devices

NEC

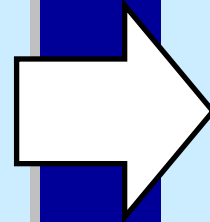
Switch size reduces to 1/30, On-resistance reduces to 1/40.

Nowadays Switch

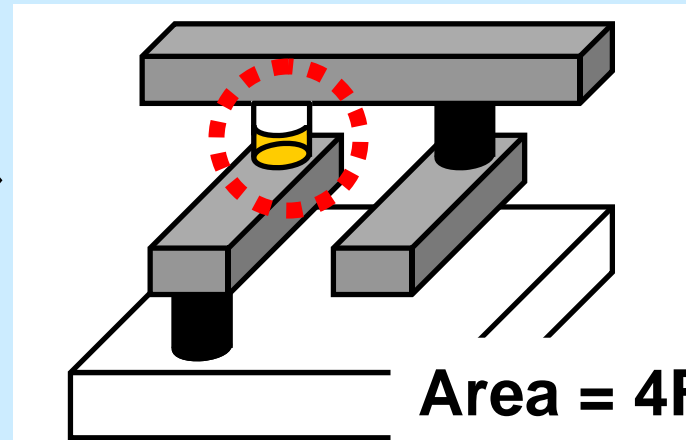


$$\text{Area} = 120F^2$$

$$\text{On-resistance} = 2\text{k}\Omega$$



Atomic Switch



$$\text{Area} = 4F^2$$

$$\text{On-resistance} = 50\Omega$$

F: minimum feature size

New device “Programmable CBIC” is proposed.

T. Sakamoto, H. Sunamura, M. Mizuno, H. Kawaura, T. Hasegawa, K. Terabe, T. Nakayama and M. Aono, IEEE J. Solid-State Circuits 40 (2005) 168.



Programmable CBIC

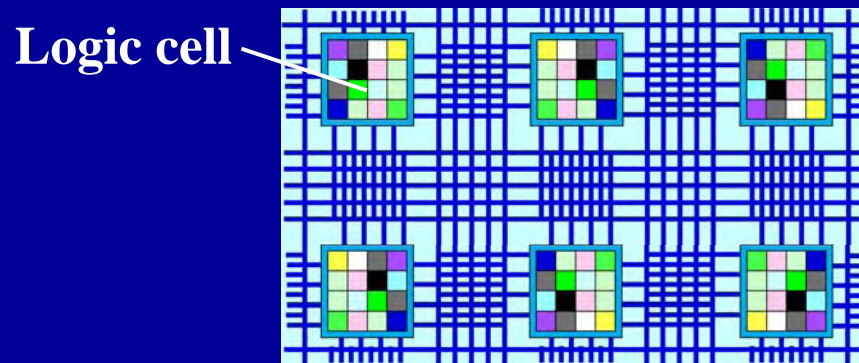
NEC

It enables many functions by a single chip

- Larger number of fine-grain logic cells
- Size reduction due to the small switches

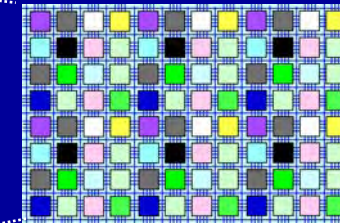


Chip size: 1/10th, or 10 times larger application
Number of programs increases vastly.



Conventional FPGA

FPGA: Field Programmable Gate Array



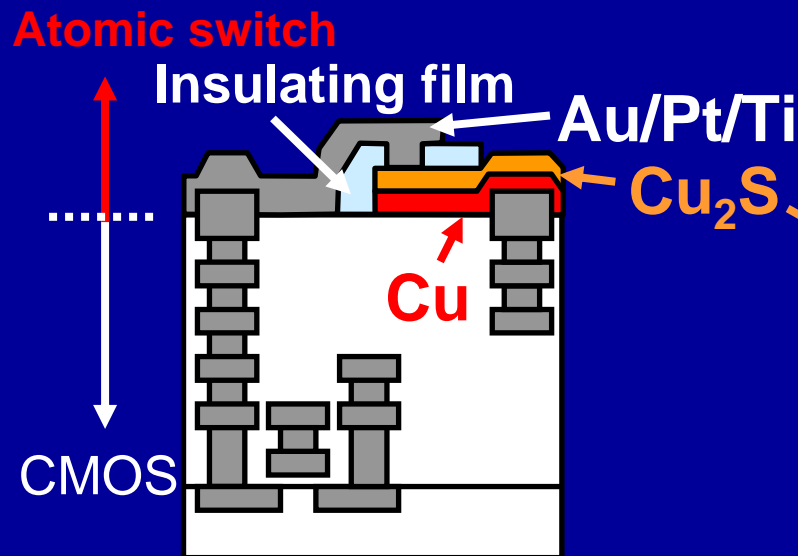
Programmable CBIC

CBIC: Cell Based Integrated Circuit



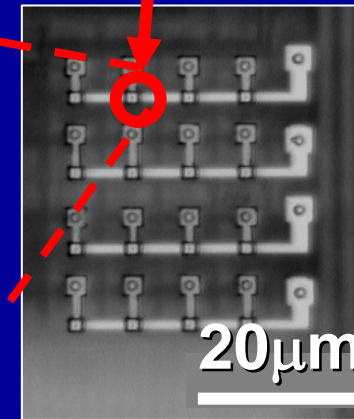
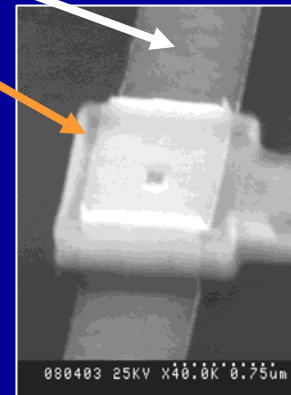
4x4 crossbar circuit

NEC

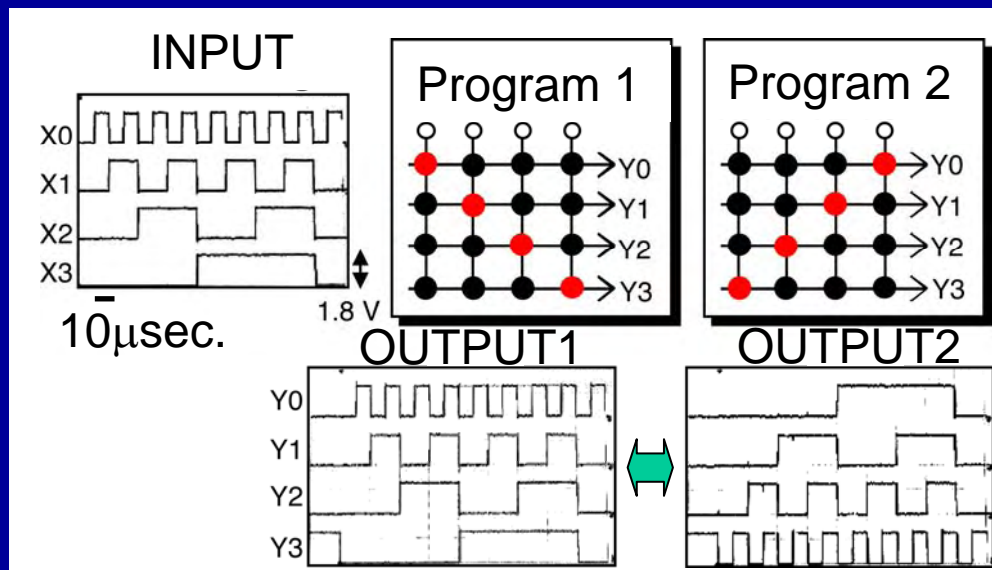


1.8V 0.18 μ m CMOS logic

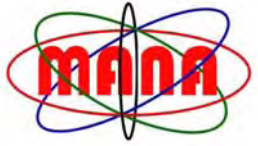
Atomic switch



4 X 4crossbar switch

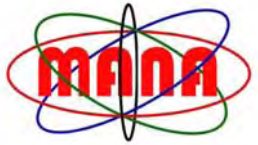


T. Sakamoto, et al.,
IEEE J. Solid-State Circuits
40 (2005) 168.



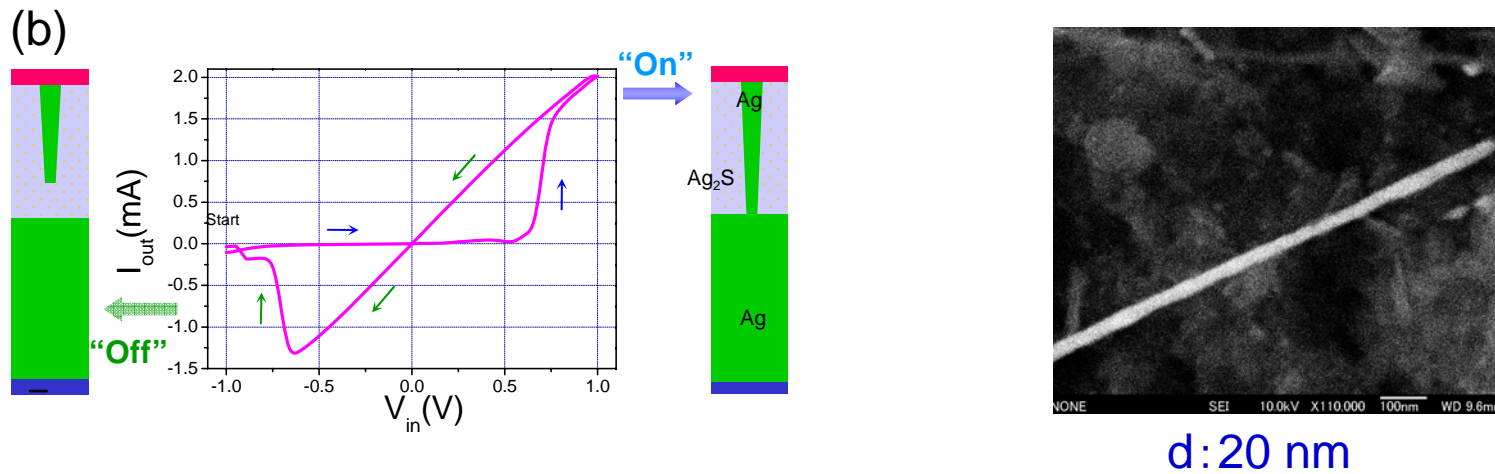
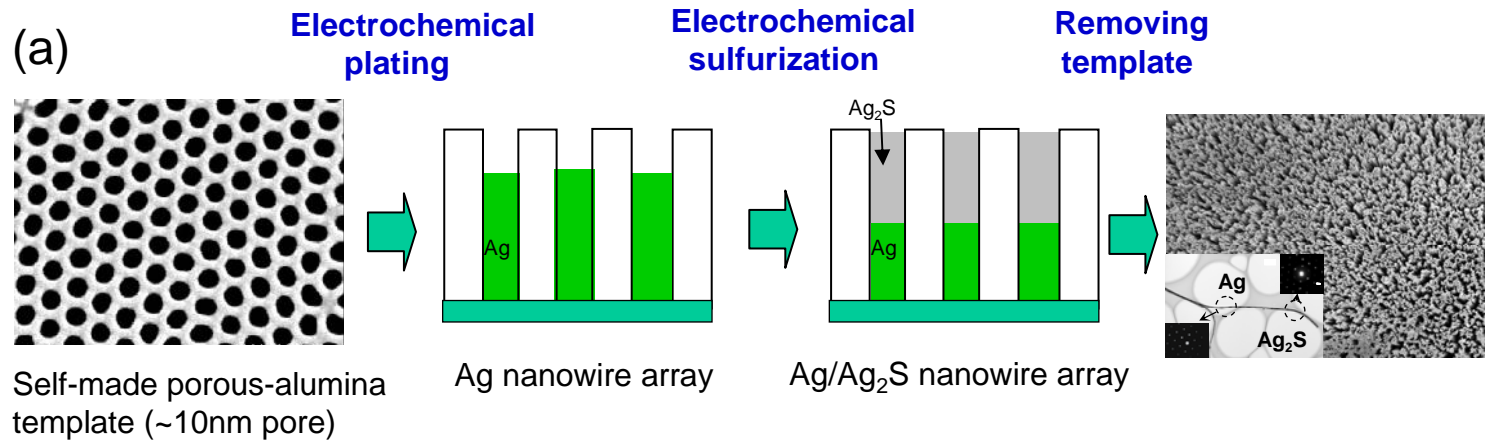
OUTLINE

1. Mechanism and Characteristics
2. Application for Commercial Devices
- 3. New Type of Atomic Switch**
 - 1) Atomic Switch Array using AAO Template
 - 2) Three terminal Atomic Switch
 - 3) Photon-assisted Atomic Switch



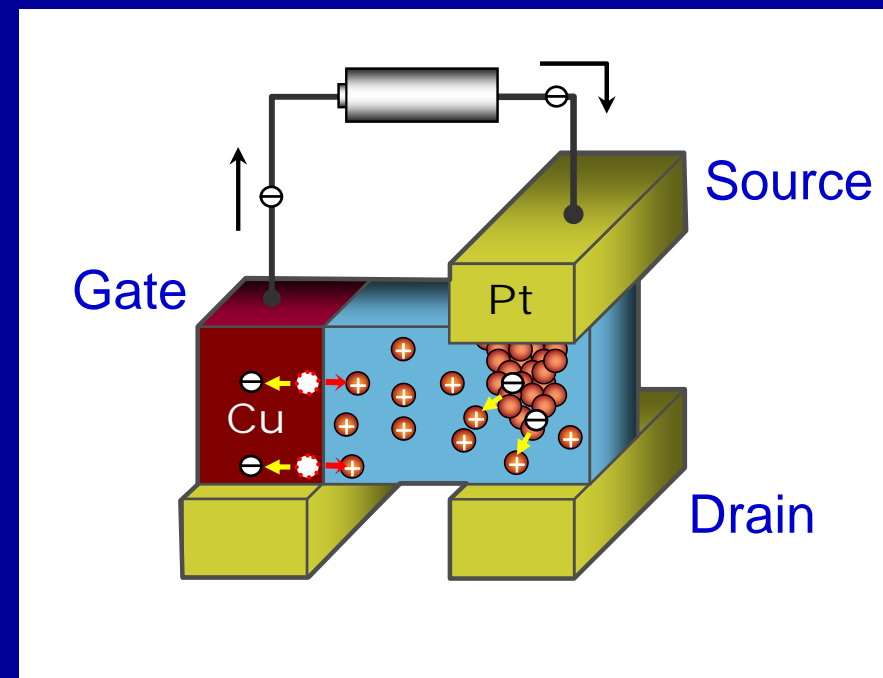
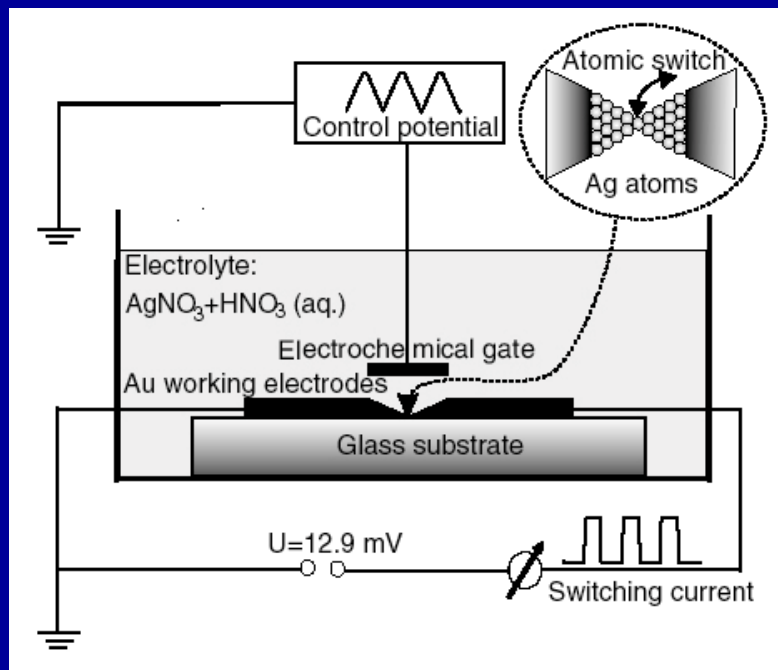
Atomic switch array using AAO

Ag₂S/Ag nanorod and its switching property



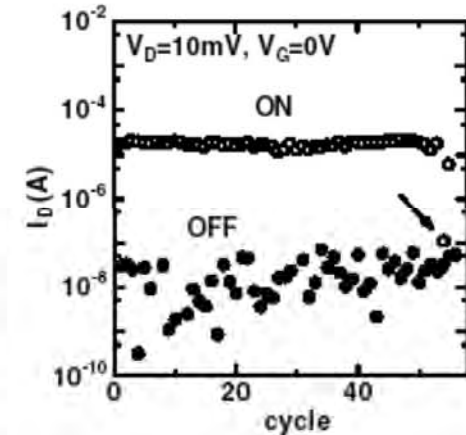
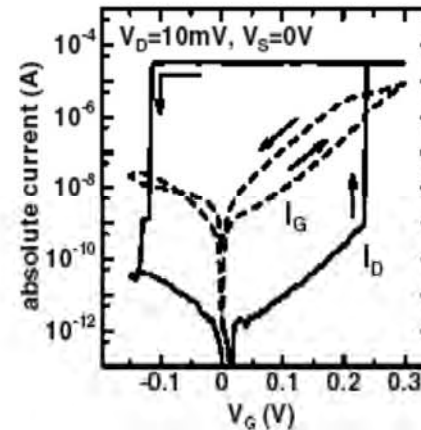
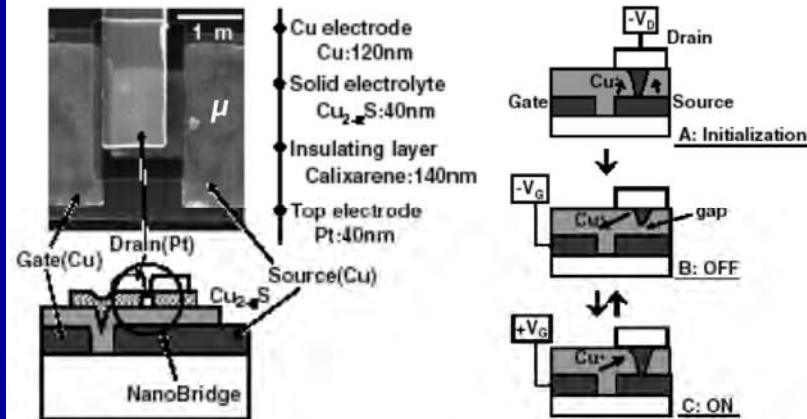
Ch. Liang, K. Terabe, T. Hasegawa, R. Negishi, T. Tamura and M. Aono, *Small* 10 (2005) 971.

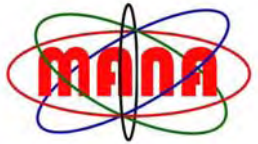
For more controllability, large current, etc.



F. Xie et al., Phys. Rev. Lett., 93, 128303 (2004).

For more controllability, large current, etc.





All functions enabled by a single chip using Atomic Switch



Ubiquitous Network



Robot



Cell phones



Digital TV

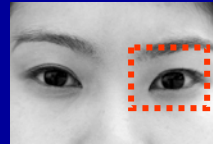


Car



High Performance Programmable Device

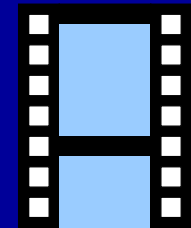
Sensor



GPS



Video decoder



Communication

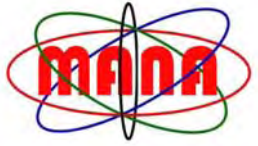


MP3 decoder



Health care





1. Mechanism and Characteristics

- 1) Atomic Switch with 1 nm gap
- 2) Gapless Atomic Switch (Nano Bridge™)

2. Application for Commercial Devices

- 1) Nonvolatile Memory
- 2) Programmable Logic Device

3. New Type of Atomic Switch

- 1) Atomic Switch Array using AAO Template
- 2) Three terminal Atomic Switch
- 3) Photon-assisted Atomic Switch